# **MCH6444**

# Power MOSFET 35V, 98mΩ, 2.5A, Single N-Channel

This Power MOSFET is produced using ON Semiconductor's trench technology, which is specifically designed to minimize gate charge and low on resistance. This device is suitable for applications with low gate charge driving or low on resistance requirements.

#### Features

- Low On-Resistance
- 4V drive
- ESD Diode-Protected Gate
- Pb-Free, Halogen Free and RoHS compliance

#### **Typical Applications**

- Load Switch
- Motor Drive

# SPECIFICATIONS

ABSOLUTE MAXIMUM RATING at Ta = 25°C (Note 1)

Parameter	Symbol	Value	Unit
Drain to Source Voltage	VDSS	35	V
Gate to Source Voltage	VGSS	±20	V
Drain Current (DC)	ID	2.5	Α
Drain Current (Pulse) PW $\leq 10\mu$ s, duty cycle $\leq 1\%$	IDP	10	А
Power Dissipation When mounted on ceramic substrate $(900mm^2 \times 0.8mm)$	PD	0.8	w
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	–55 to +150	°C

Note 1 : Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

#### THERMAL RESISTANCE RATINGS

Parameter	Symbol	Value	Unit
Junction to Ambient When mounted on ceramic substrate ( $900mm^2 \times 0.8mm$ )	R <sub>θJA</sub>	156.2	°C/W

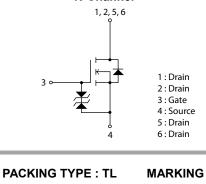


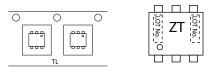
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VDSS	RDS(on) Max	ID Max
	98mΩ@_10V	Divida
35V	166mΩ@ 4.5V	2.5A
	201mΩ@ 4V	







#### ORDERING INFORMATION

See detailed ordering and shipping information on page 5 of this data sheet.

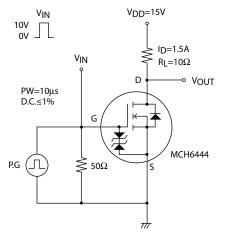
# MCH6444

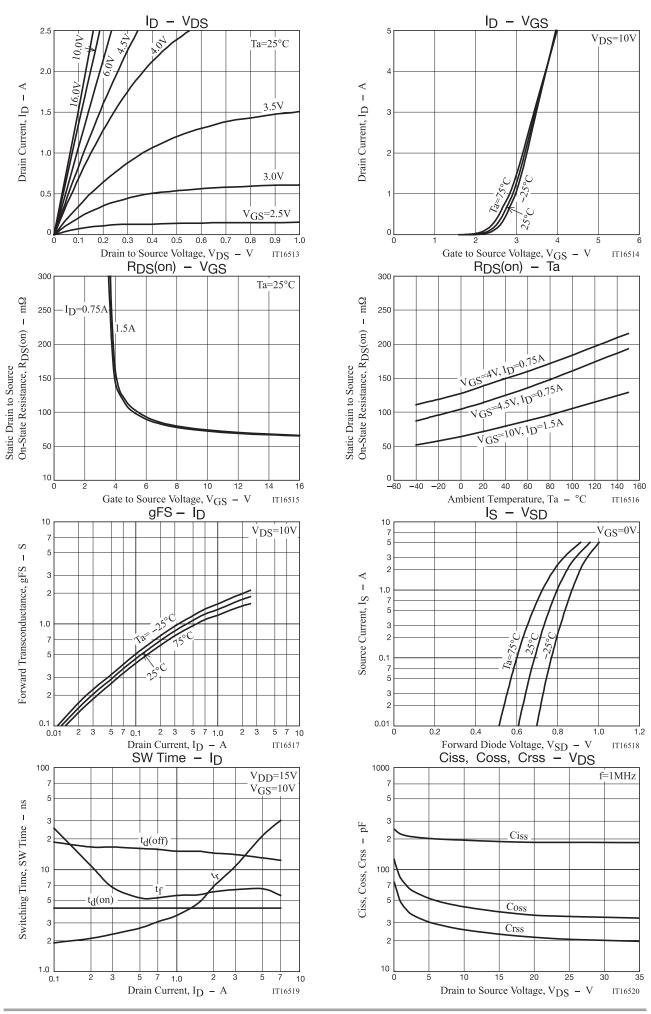
Deventer	Cumhal	Conditions	Value			1.1
Parameter	Symbol	Conditions	min	typ	max	Unit
Drain to Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0V	35			V
Zero-Gate Voltage Drain Current	IDSS	V <sub>DS</sub> =35V, V <sub>GS</sub> =0V			1	μΑ
Gate to Source Leakage Current	IGSS	V <sub>GS</sub> =±16V, V <sub>DS</sub> =0V			±10	μΑ
Gate Threshold Voltage	VGS(th)	V <sub>DS</sub> =10V, I <sub>D</sub> =1mA	1.2		2.6	V
Forward Transconductance	9FS	V <sub>DS</sub> =10V, I <sub>D</sub> =1.5A		1.7		S
	R <sub>DS</sub> (on)1	ID=1.5A, VGS=10V		75	98	mΩ
Static Drain to Source On-State Resistance	R <sub>DS</sub> (on)2	ID=0.75A, VGS=4.5V		118	166	mΩ
Resistance	R <sub>DS</sub> (on)3	on)3 ID=0.75A, VGS=4V		143	201	mΩ
Input Capacitance	Ciss			186		pF
Output Capacitance	Coss	V <sub>DS</sub> =20V, f=1MHz		36		pF
Reverse Transfer Capacitance	Crss			22		pF
Turn-ON Delay Time	t <sub>d</sub> (on)			4.2		ns
Rise Time	tr	Case an aptillard Taset Circuit		4.7		ns
Turn-OFF Delay Time	t <sub>d</sub> (off)	See specified Test Circuit		15		ns
Fall Time	tf			5.7		ns
Total Gate Charge	Qg			4		nC
Gate to Source Charge	Qgs	V <sub>DS</sub> =20V, V <sub>GS</sub> =10V, I <sub>D</sub> =2.5A		0.9		nC
Gate to Drain "Miller" Charge	Qgd	]		0.7		nC
Forward Diode Voltage	V <sub>SD</sub>	IS=2.5A, VGS=0V		0.86	1.2	V

#### **ELECTRICAL CHARACTERISTICS** at Ta = 25°C (Note 2)

Note 2 : Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

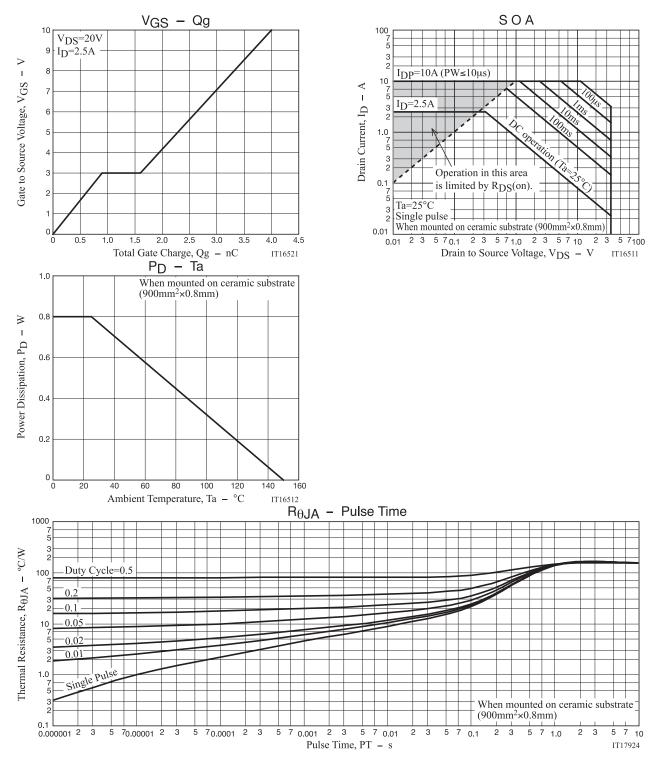
### Switching Time Test Circuit





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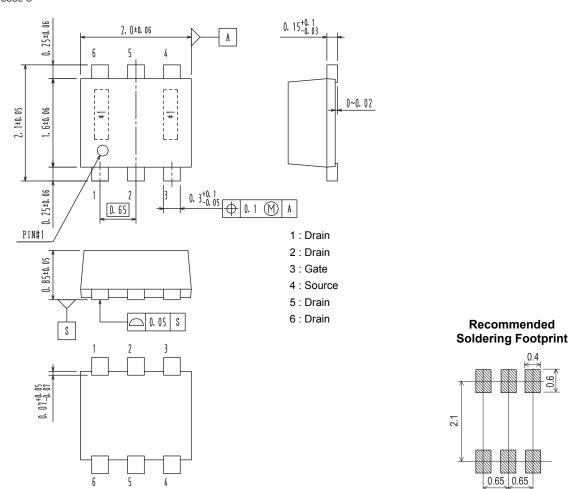
## MCH6444



### PACKAGE DIMENSIONS

unit : mm

SC-88FL / MCPH6 CASE 419AS ISSUE O



#### **ORDERING INFORMATION**

Device	Marking	Package	Shipping (Qty / Packing)	
MCH6444-TL-H	ZT	SC-88FL / MCPH6	3,000 / Tape & Reel	
MCH6444-TL-W	Σι	(Pb-Free / Halogen Free)		

+ For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D. http://www.onsemi.com/pub\_link/Collateral/BRD8011-D.PDF

# Note on usage : Since the MCH6444 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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